

MOSFET – Power, N-Channel, DPAK

14 A, 25 V

NTD14N03R, NVD14N03R

Features

- Planar HD3e Process for Fast Switching Performance
- Low $R_{DS(on)}$ to Minimize Conduction Loss
- Low C_{iss} to Minimize Driver Loss
- Low Gate Charge
- Optimized for High Side Switching Requirements in High-Efficiency DC-DC Converters
- NVD and SVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

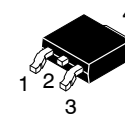
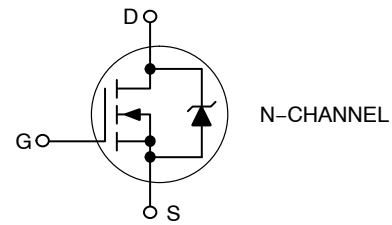
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	25	Vdc
Gate-to-Source Voltage – Continuous	V_{GS}	± 20	Vdc
Thermal Resistance – Junction-to-Case	$R_{\theta JC}$	6.0	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	20.8	W
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$, Chip	I_D	14	A
– Continuous @ $T_A = 25^\circ\text{C}$, Limited by Package	I_D	11.4	A
– Single Pulse ($t_p \leq 10 \mu\text{s}$)	I_D	28	A
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	80	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	1.56	W
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$	I_D	3.1	A
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	120	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	1.04	W
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$	I_D	2.5	A
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

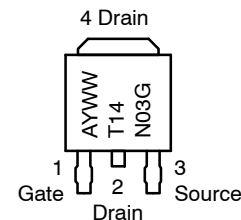
- When surface mounted to an FR4 board using 0.5 sq. in pad size.
- When surface mounted to an FR4 board using minimum recommended pad size.

14 AMPERES, 25 VOLTS
 $R_{DS(on)} = 70.4 \text{ m}\Omega$ (Typ)



DPAK
CASE 369C
(Surface Mount)
STYLE 2

MARKING DIAGRAM & PIN ASSIGNMENTS



A = Assembly Location*
Y = Year
WW = Work Week
14N03 = Device Code
G = Pb-Free Package

* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 5.

NTD14N03R, NVD14N03R

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Characteristics	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (Note 3) (V _{GS} = 0 Vdc, I _D = 250 μ Adc) Temperature Coefficient (Positive)	V _{(br)DSS}	25 –	28 –	– –	Vdc mV/°C
Zero Gate Voltage Drain Current (V _{DS} = 20 Vdc, V _{GS} = 0 Vdc) (V _{DS} = 20 Vdc, V _{GS} = 0 Vdc, T _J = 150°C)	I _{DSS}	– –	– –	1.0 10	μ Adc
Gate-Body Leakage Current (V _{GS} = $\pm$ 20 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	–	–	$\pm$ 100	nAdc

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage (Note 3) (V _{DS} = V _{GS} , I _D = 250 μ Adc) Threshold Temperature Coefficient (Negative)	V _{GS(th)}	1.0 –	1.5 –	2.0 –	Vdc mV/°C
Static Drain-to-Source On-Resistance (Note 3) (V _{GS} = 4.5 Vdc, I _D = 5 Adc) (V _{GS} = 10 Vdc, I _D = 5 Adc)	R _{DS(on)}	– –	117 70.4	130 95	m Ω
Forward Transconductance (Note 3) (V _{DS} = 10 Vdc, I _D = 5 Adc)	g _{FS}	–	7.0	–	Mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{DS} = 20 Vdc, V _{GS} = 0 V, f = 1 MHz)	C _{iss}	–	115	–	pF
Output Capacitance		C _{oss}	–	62	–	
Transfer Capacitance		C _{rss}	–	33	–	

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	(V _{GS} = 10 Vdc, V _{DD} = 10 Vdc, I _D = 5 Adc, R _G = 3 Ω)	t _{d(on)}	–	3.8	–	ns
Rise Time		t _r	–	27	–	
Turn-Off Delay Time		t _{d(off)}	–	9.6	–	
Fall Time		t _f	–	2.0	–	
Gate Charge	(V _{GS} = 5 Vdc, I _D = 5 Adc, V _{DS} = 10 Vdc) (Note 3)	Q _T	–	1.8	–	nC
		Q ₁	–	0.8	–	
		Q ₂	–	0.7	–	

SOURCE-DRAIN DIODE CHARACTERISTICS

Forward On-Voltage	(I _S = 5 Adc, V _{GS} = 0 Vdc) (Note 3) (I _S = 5 Adc, V _{GS} = 0 Vdc, T _J = 125°C)	V _{SD}	– –	0.93 0.82	1.2 –	Vdc
Reverse Recovery Time	(I _S = 5 Adc, V _{GS} = 0 Vdc, di _S /dt = 100 A/ μ s) (Note 3)	t _{rr}	–	6.6	–	ns
		t _a	–	4.75	–	
		t _b	–	1.88	–	
Reverse Recovery Stored Charge		Q _{RR}	–	0.002	–	μ C

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width $\leq$ 300 μ s, Duty Cycle $\leq$ 2%.

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

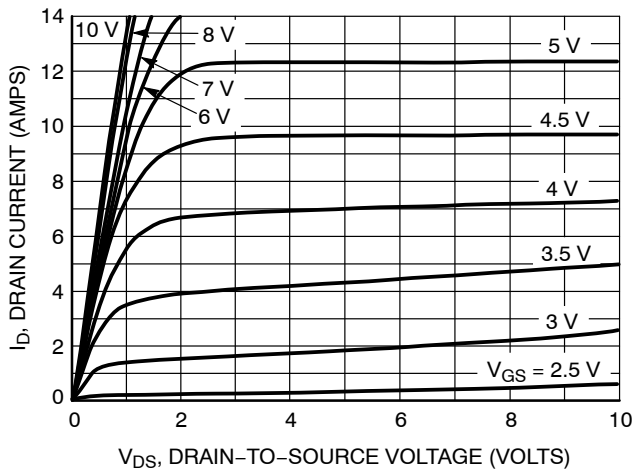


Figure 1. On-Region Characteristics

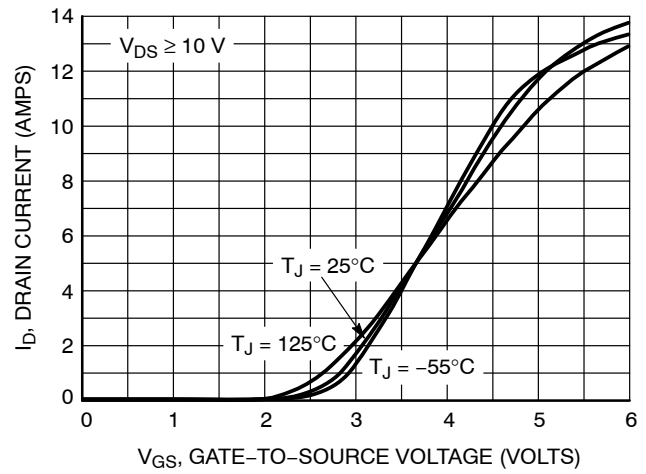


Figure 2. Transfer Characteristics

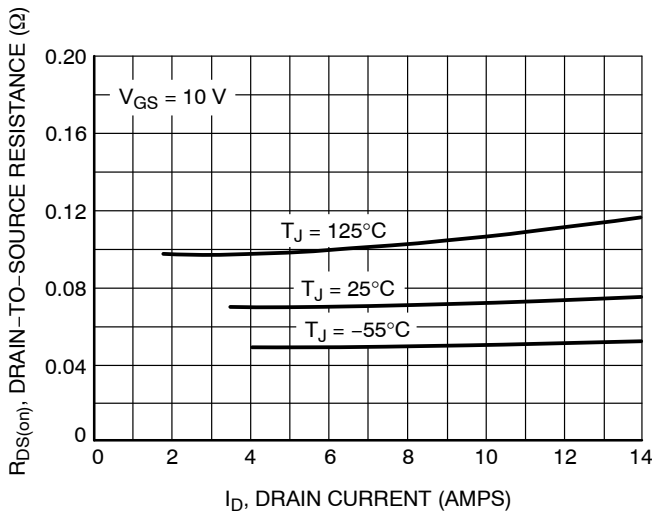


Figure 3. On-Resistance versus Drain Current and Temperature

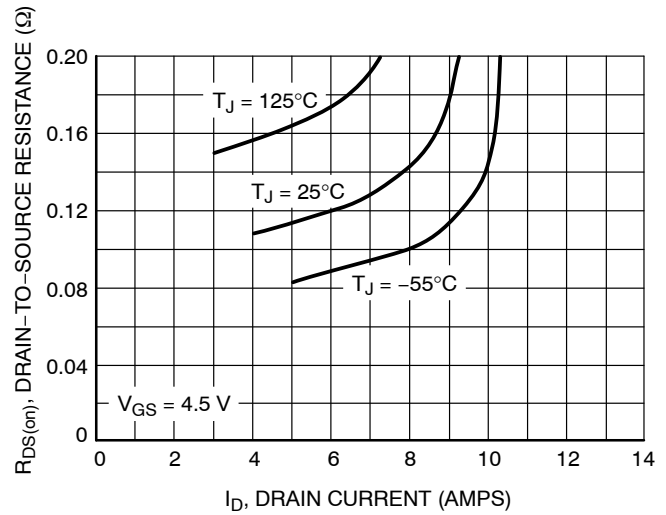


Figure 4. On-Resistance versus Drain Current and Temperature

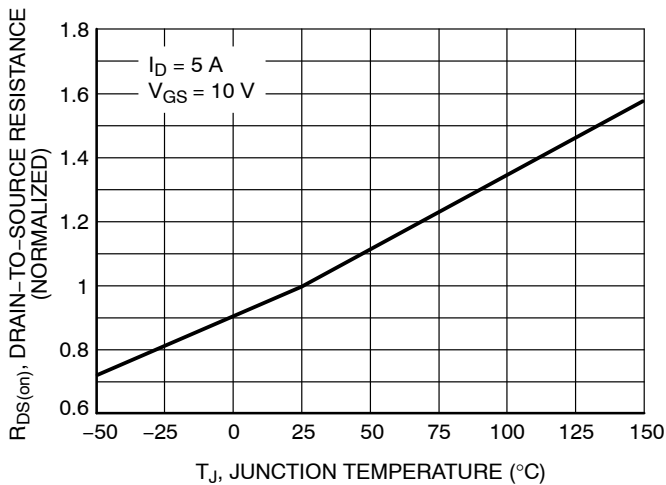


Figure 5. On-Resistance Variation with Temperature

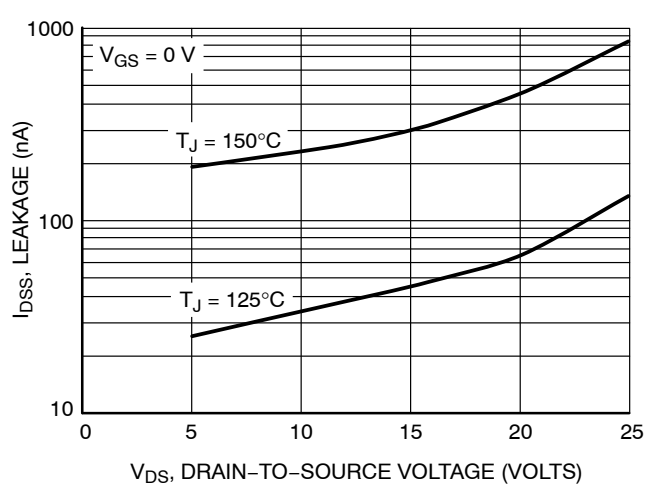


Figure 6. Drain-to-Source Leakage Current versus Voltage

NTD14N03R, NVD14N03R

TYPICAL CHARACTERISTICS

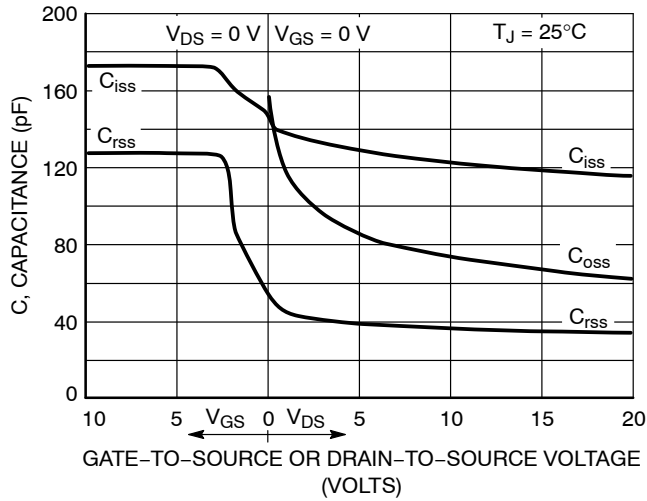


Figure 7. Capacitance Variation

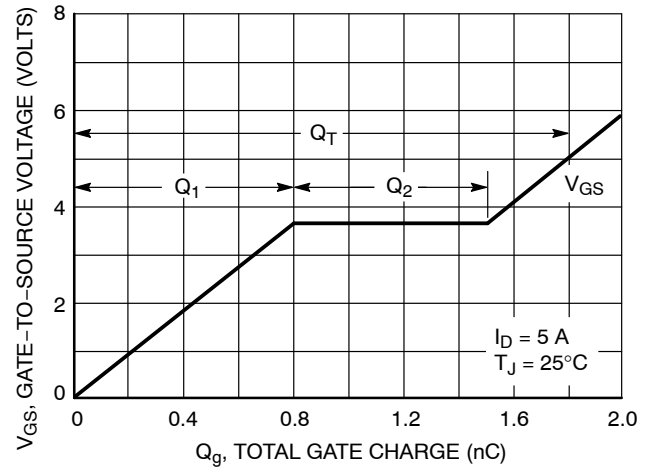


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

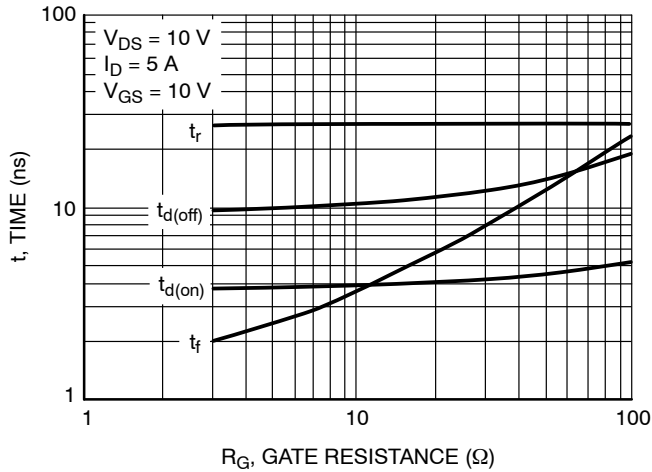


Figure 9. Resistive Switching Time Variation versus Gate Resistance

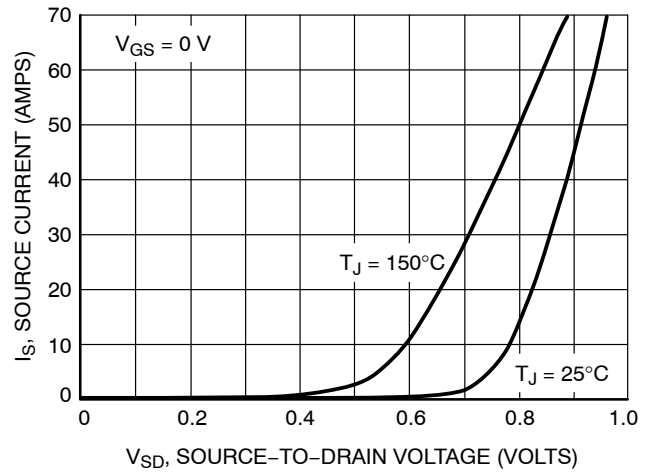


Figure 10. Diode Forward Voltage versus Current

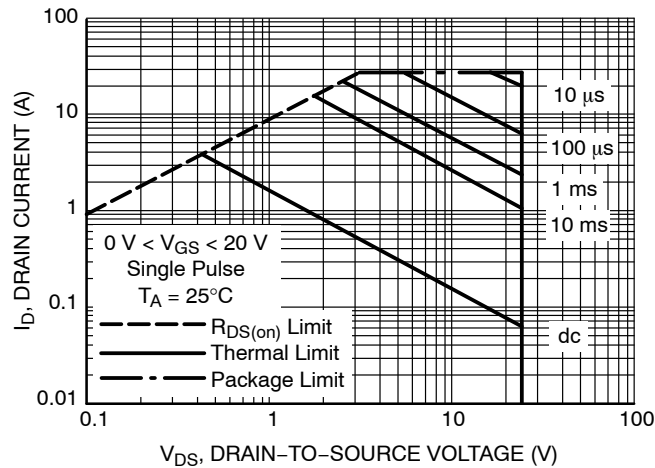


Figure 11. Maximum Rated Forward Biased Safe Operating Area

NTD14N03R, NVD14N03R

TYPICAL CHARACTERISTICS

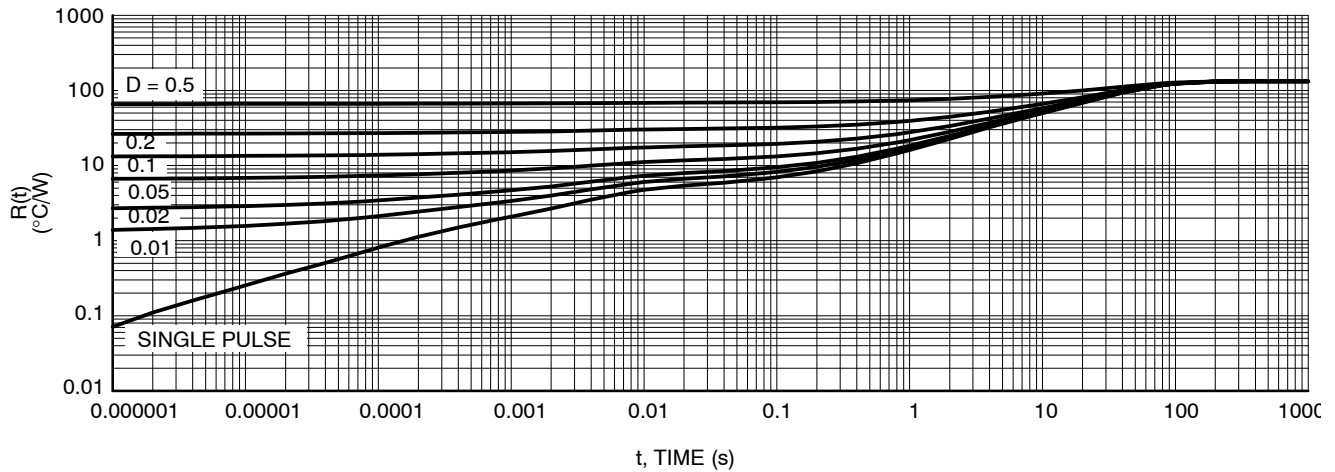


Figure 12. Thermal Response

ORDERING INFORMATION

Device	Package	Shipping [†]
NTD14N03RT4G	DPAK (Pb-Free)	2500 / Tape & Reel

DISCONTINUED (Note 5)

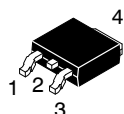
NVD14N03RT4G*	DPAK (Pb-Free)	2500 / Tape & Reel
SVD14N03RT4G*	DPAK (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NVD and SVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

5. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

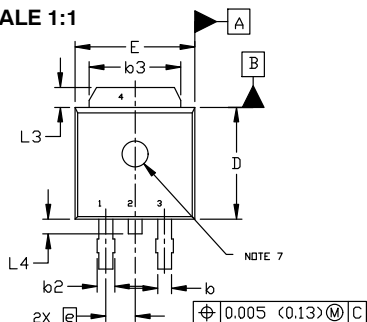
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



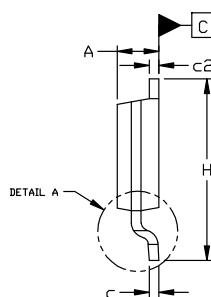
DPAK (SINGLE GAUGE) CASE 369C ISSUE G

DATE 31 MAY 2023

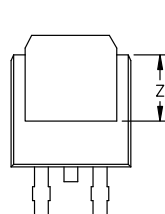
SCALE 1:1



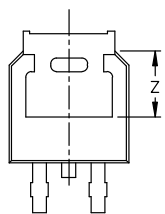
TOP VIEW



SIDE VIEW

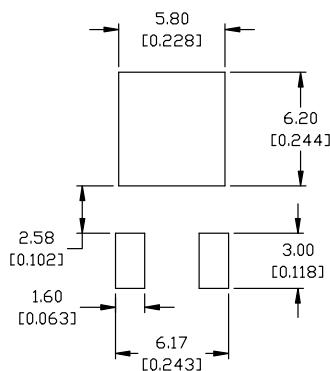


BOTTOM VIEW



BOTTOM VIEW

ALTERNATE
CONSTRUCTIONS



RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 1:

PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:

PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:

PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:

PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:

PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:

PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:

PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 8:

PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE

STYLE 9:

PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE

STYLE 10:

PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

NOTES:

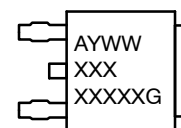
1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	----	0.040	---	1.01
Z	0.155	----	3.93	---

GENERIC MARKING DIAGRAM*



IC



Discrete

XXXXXX = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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